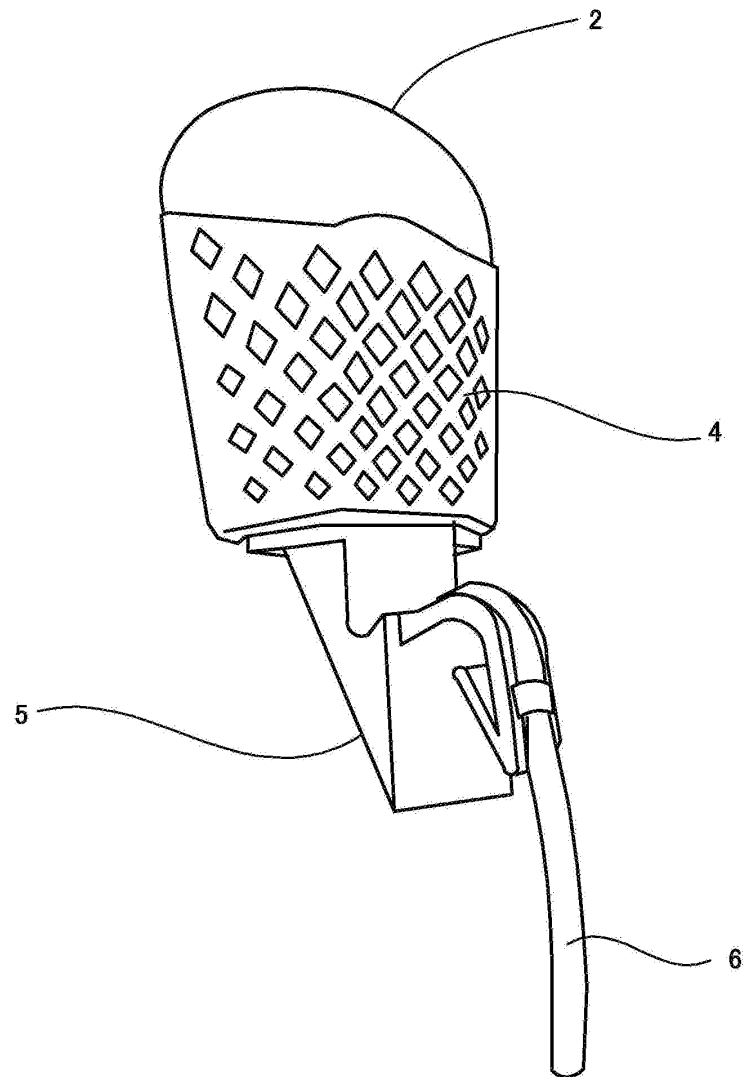
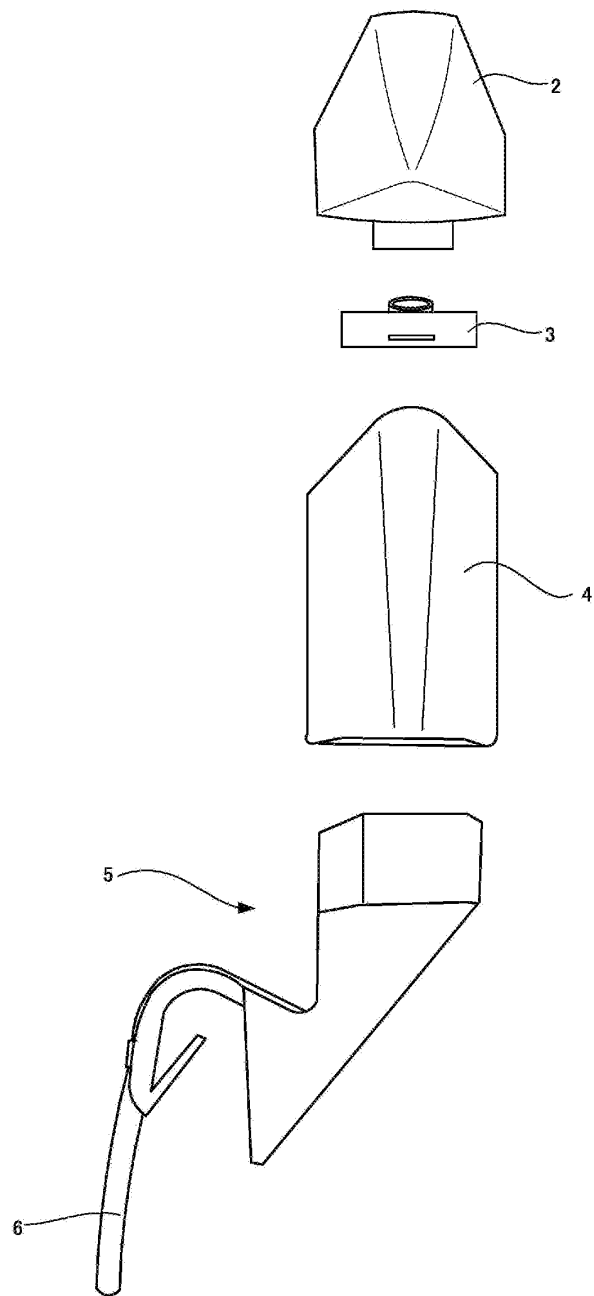


[図1]



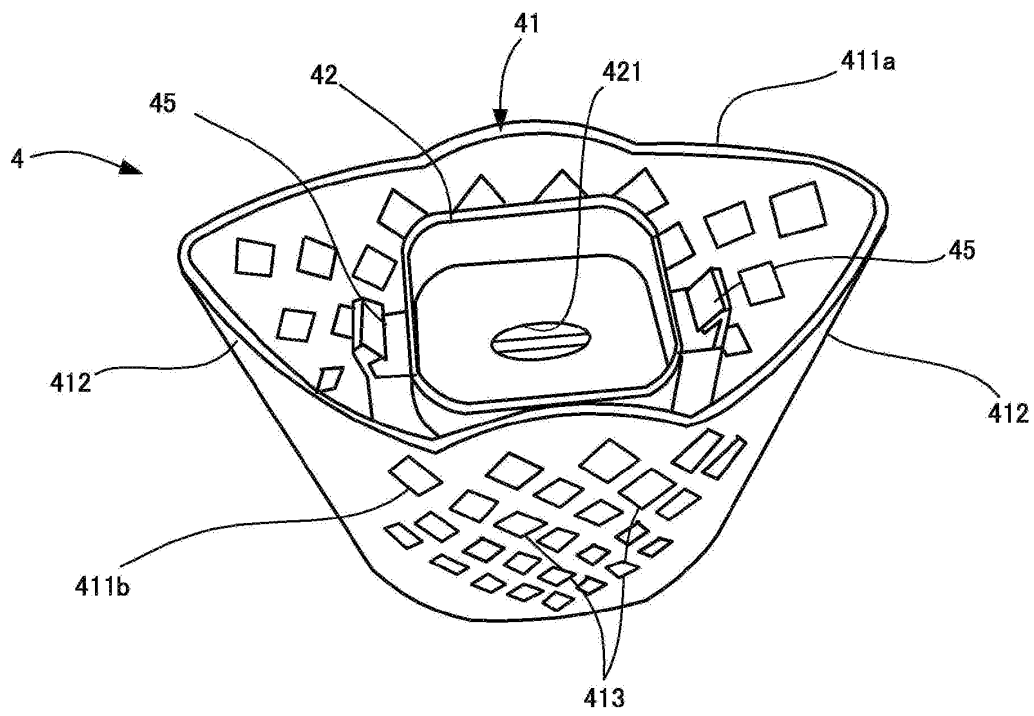
[図2]



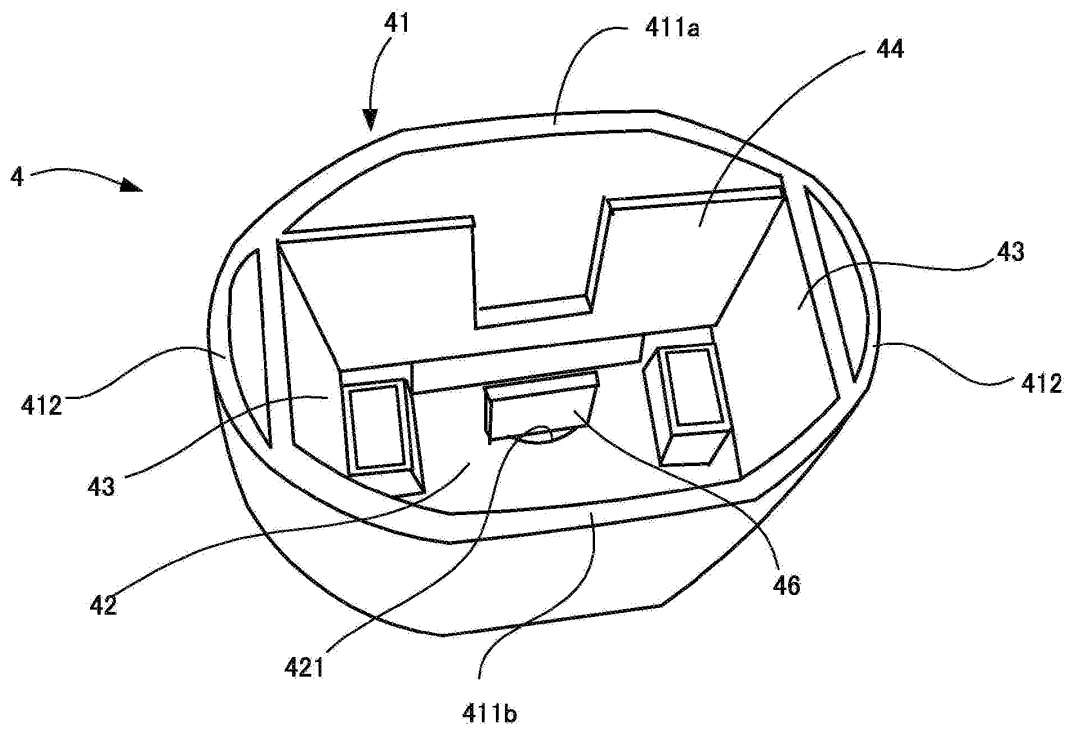
A cross-sectional view of a semiconductor device 100. The device includes a substrate 11 with a top surface 111. A layer 12 is formed on the top surface 111. The layer 12 has a central opening 121 and side openings 122. The side openings 122 are formed in the layer 12 and extend to the top surface 111. The central opening 121 is a rectangular opening in the layer 12. The side openings 122 are rectangular openings in the layer 12, extending to the top surface 111. The layer 12 is formed on the top surface 111 of the substrate 11.

Figure 1 is a perspective view of a head-mounted display (HMD) 2. The HMD includes a main body 21 and a display unit 22. The display unit 22 is positioned at the bottom of the main body 21 and includes a display area 211 and a frame 222.

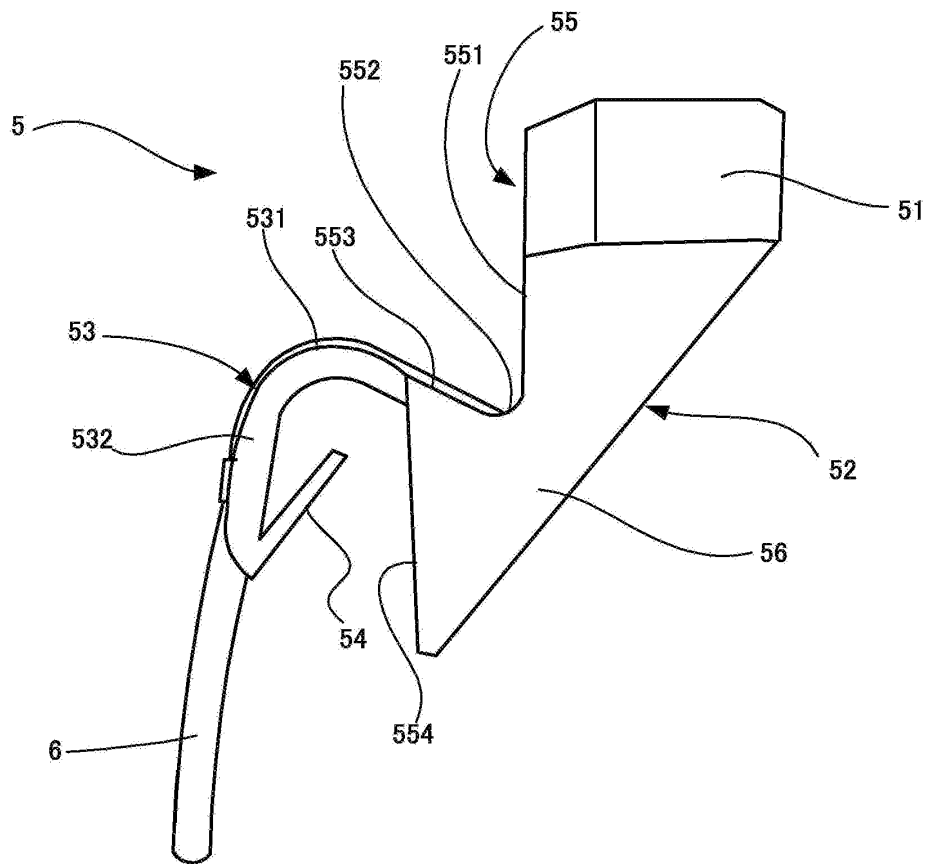
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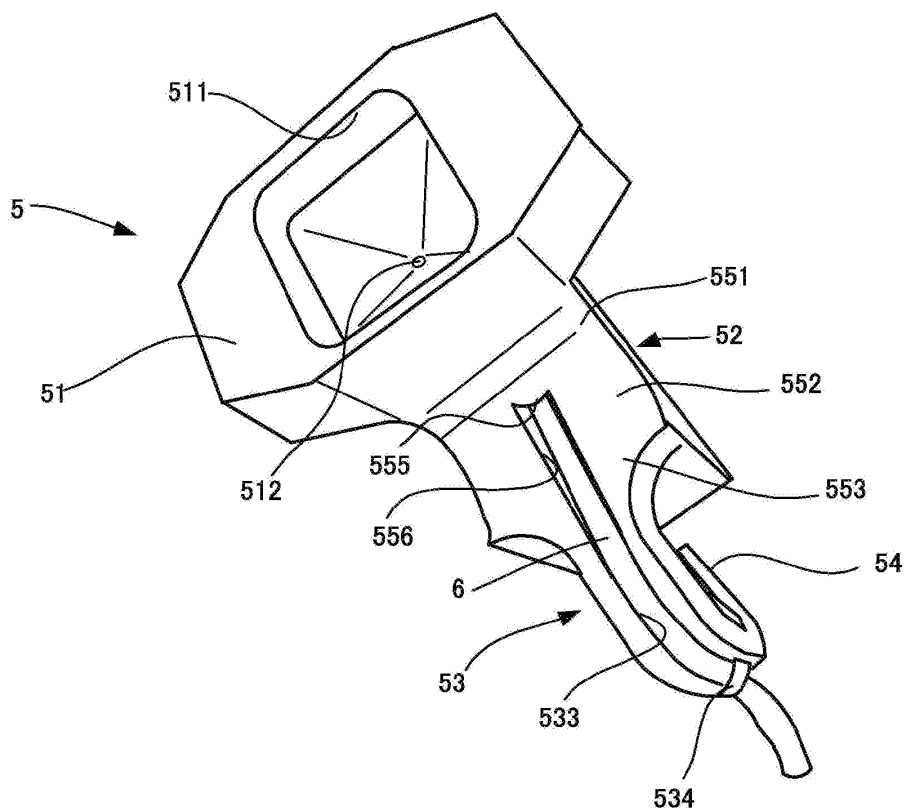
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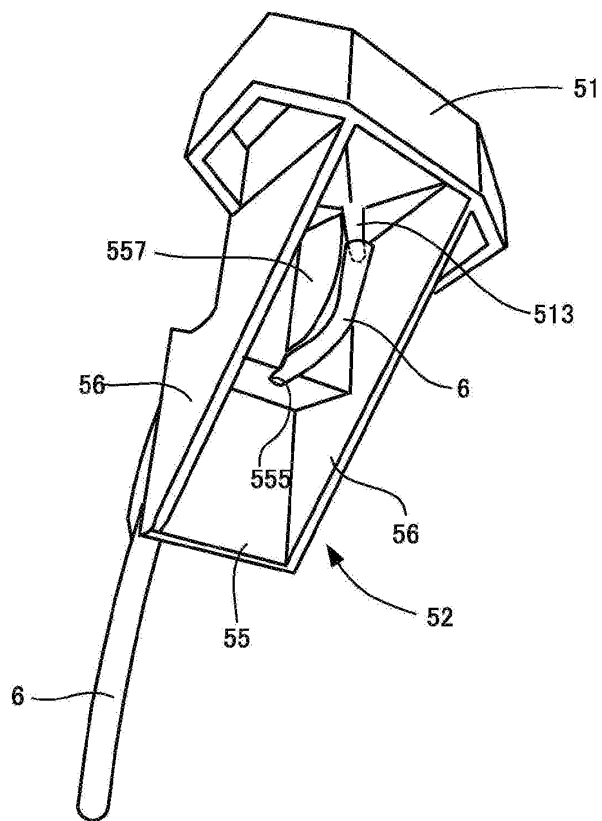
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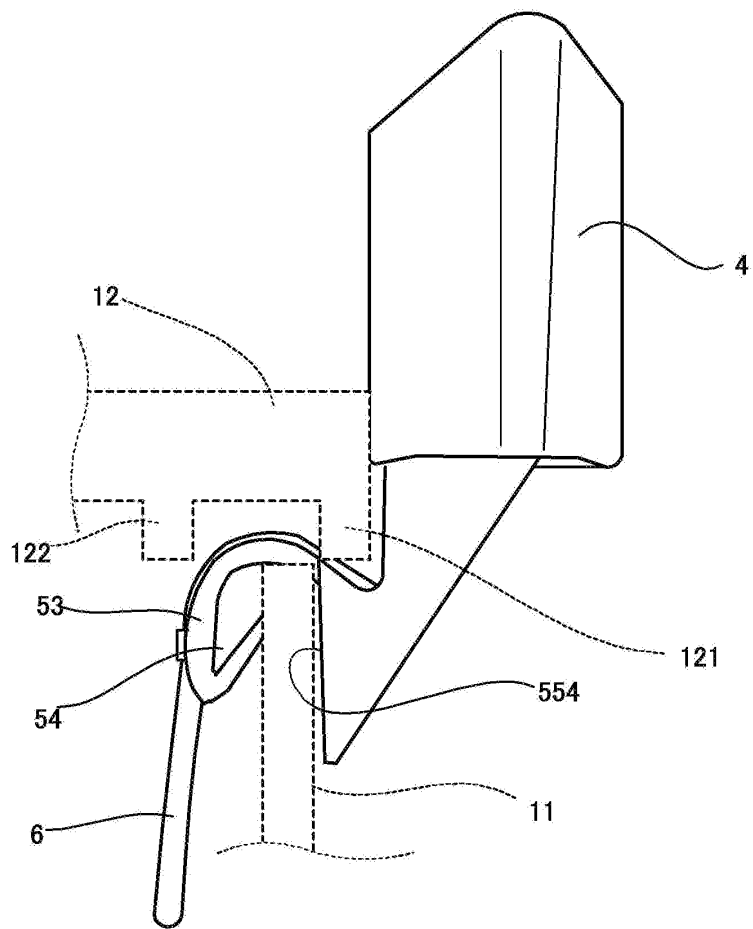
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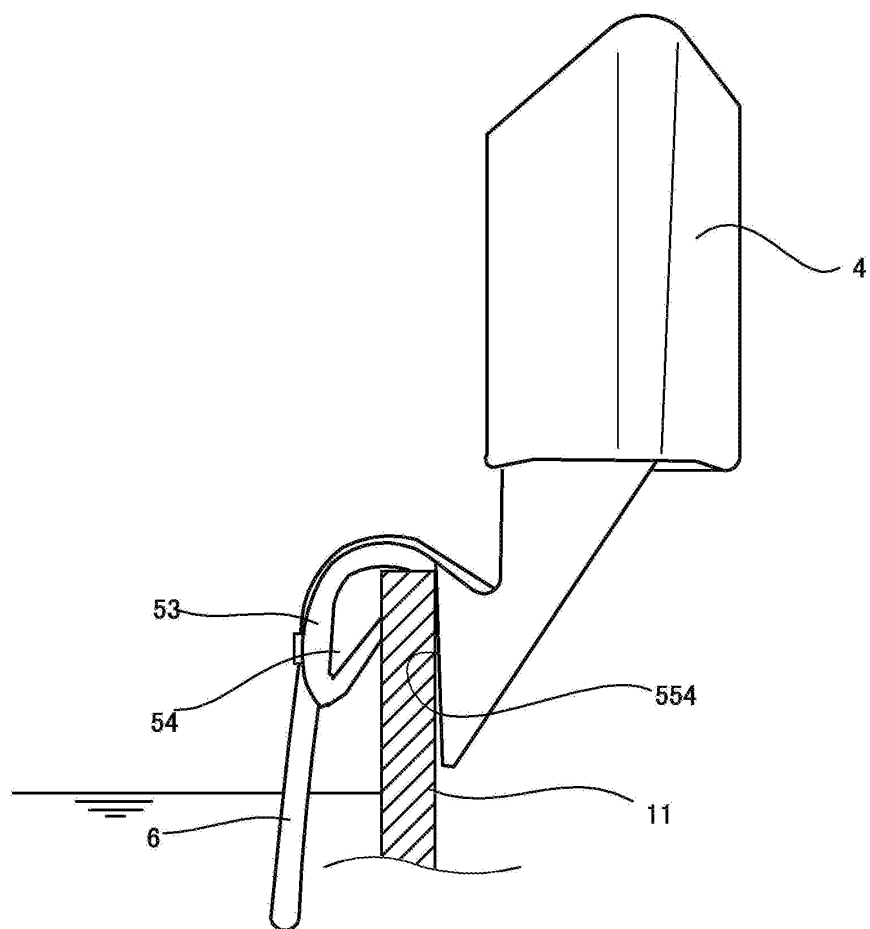
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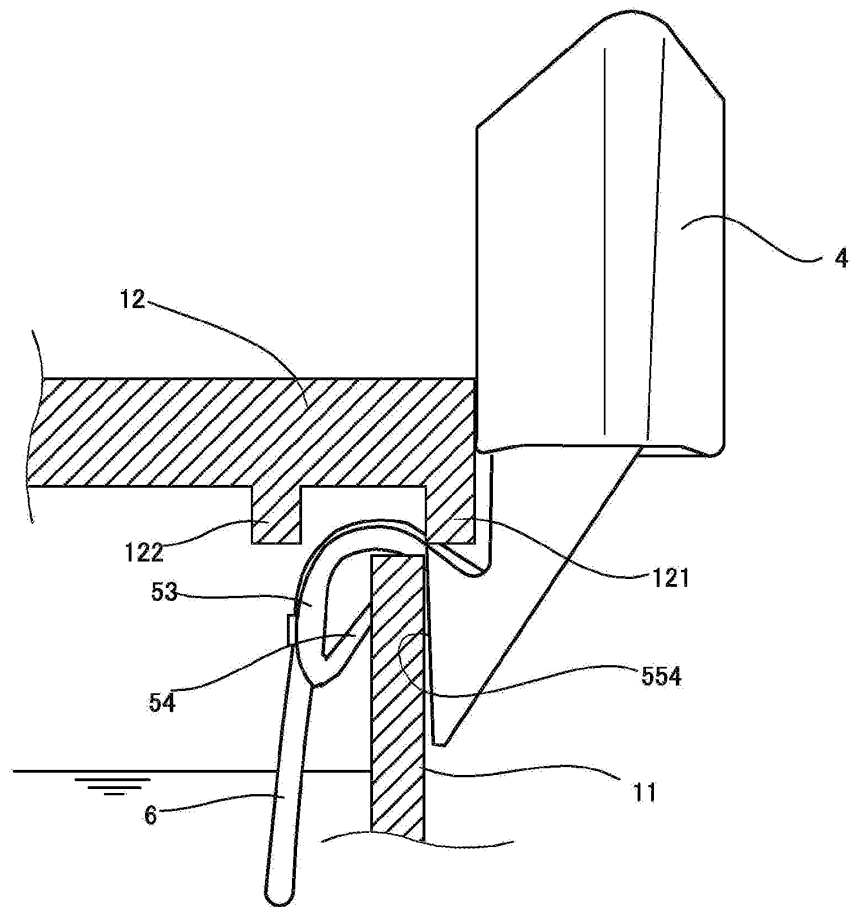
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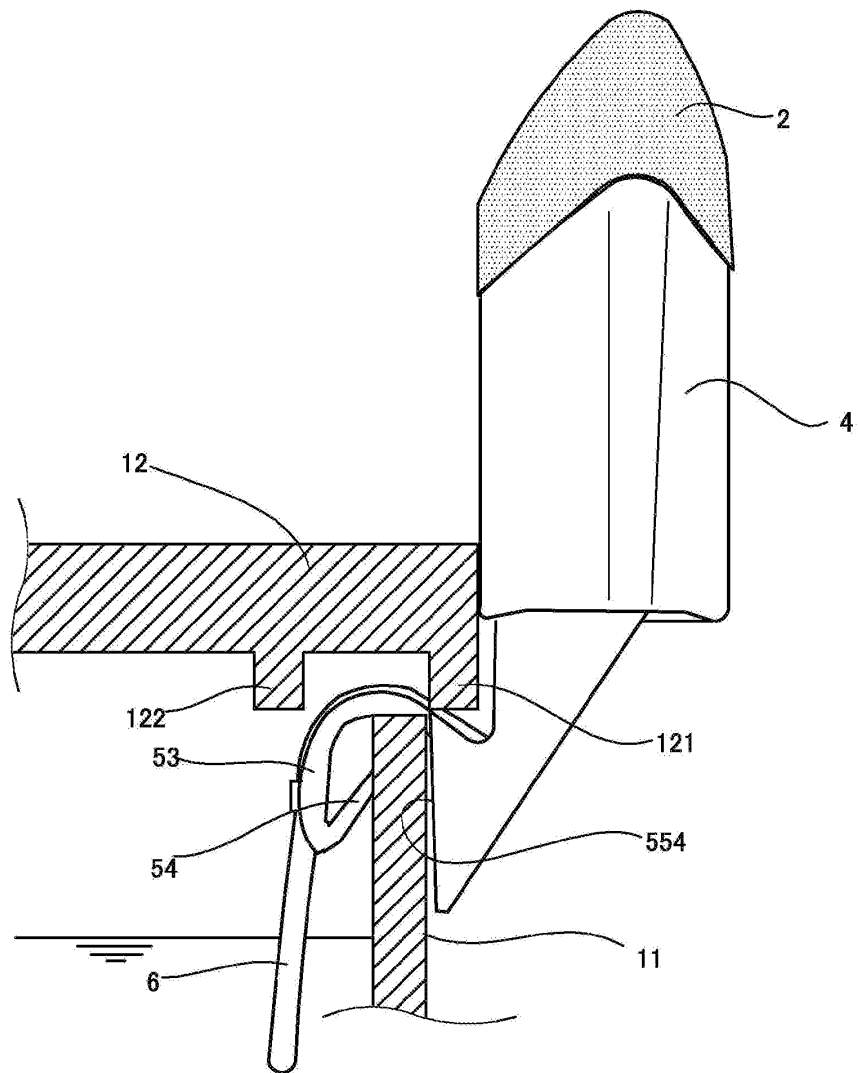
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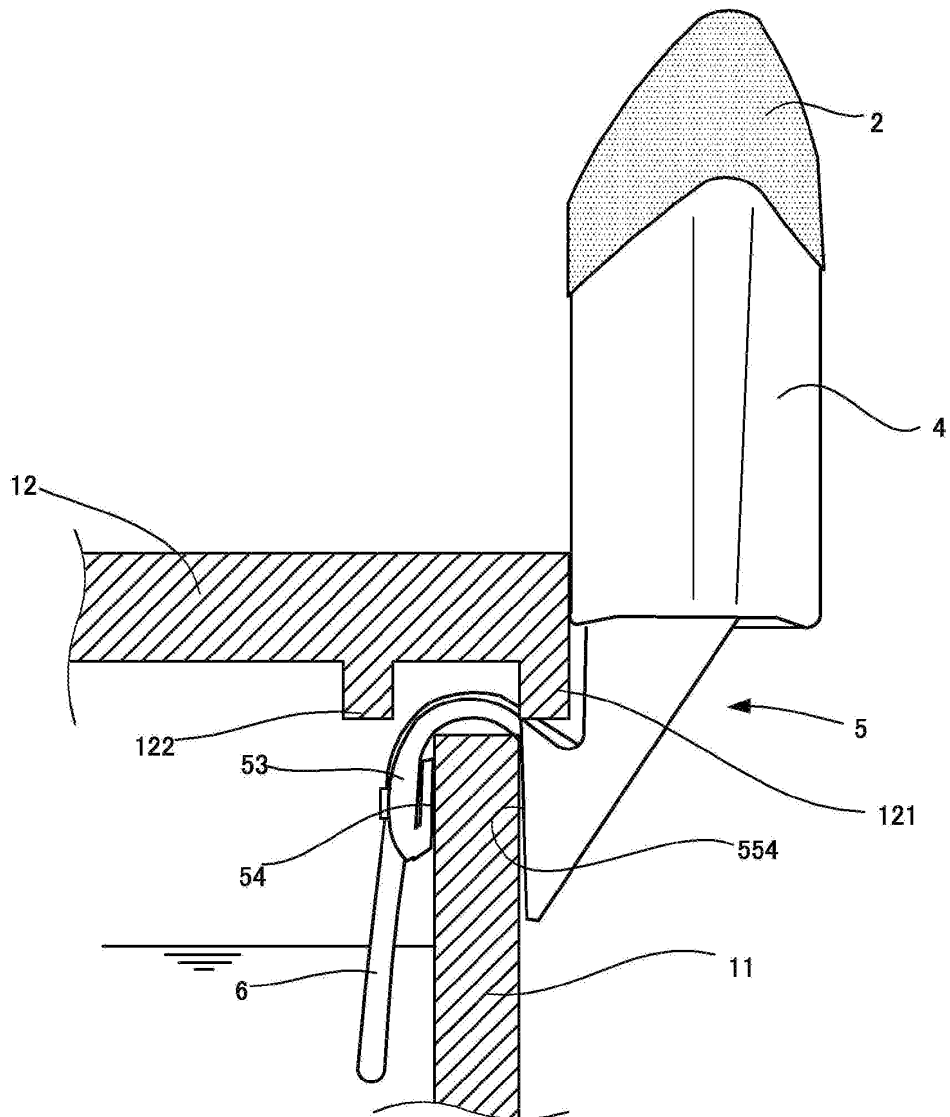
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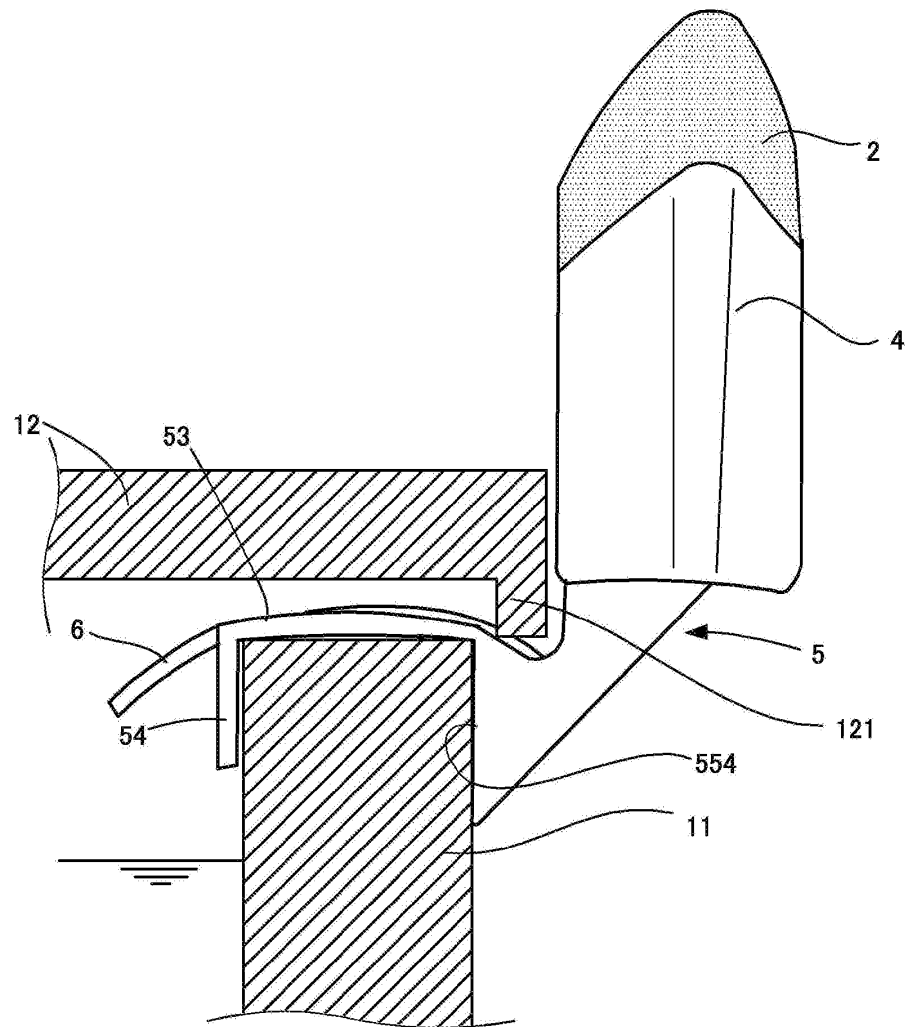
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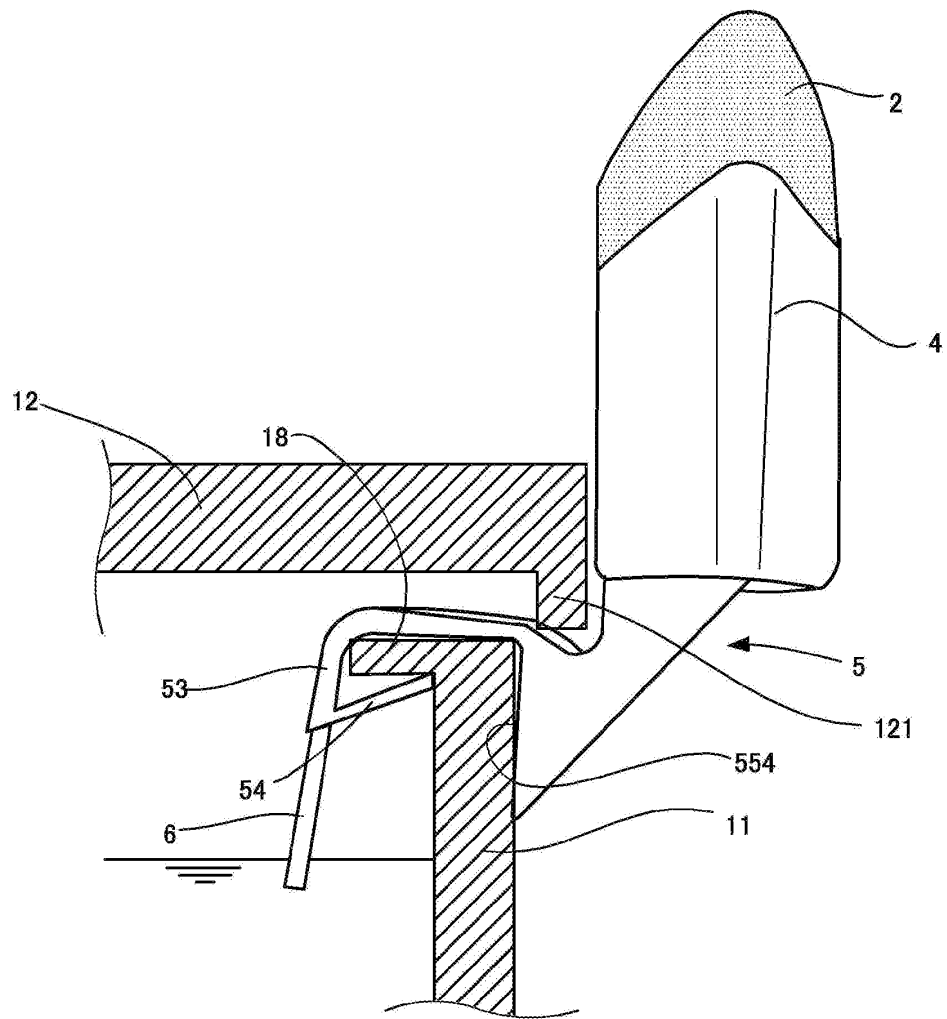
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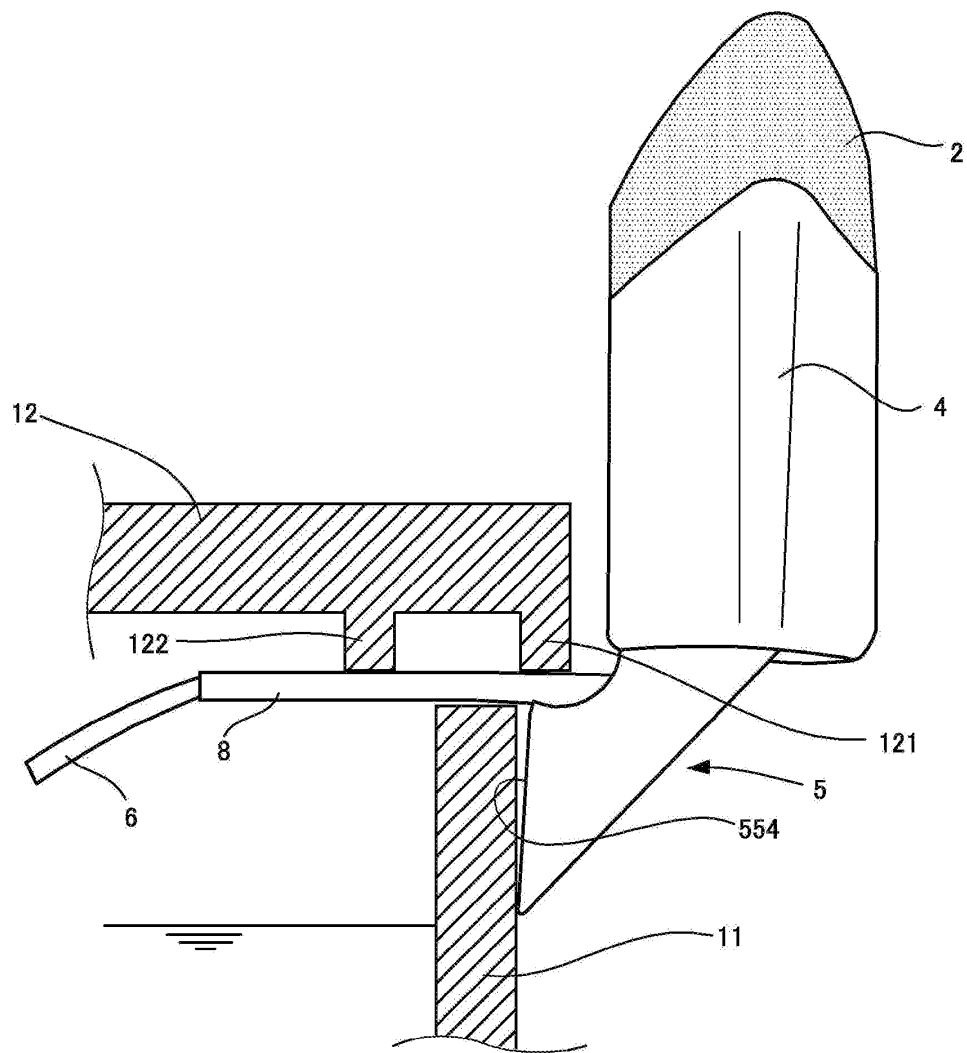
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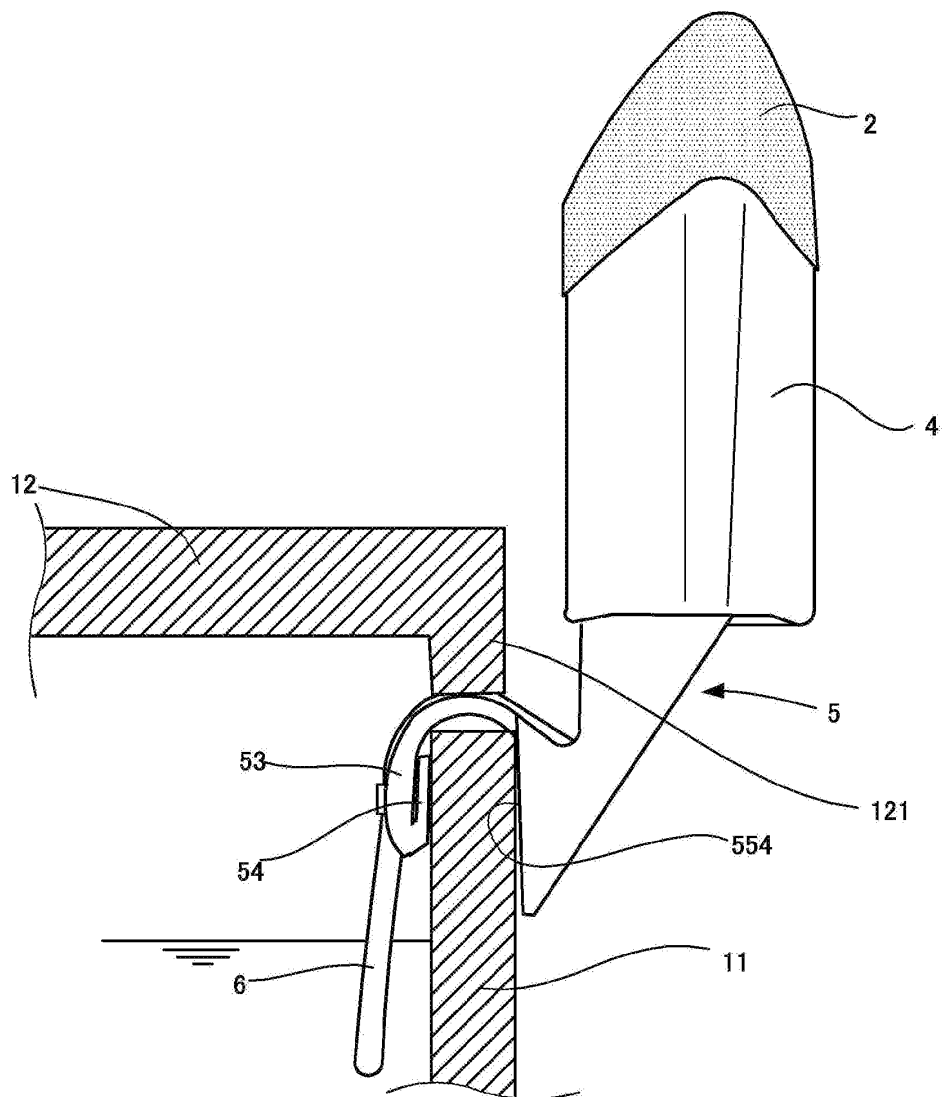
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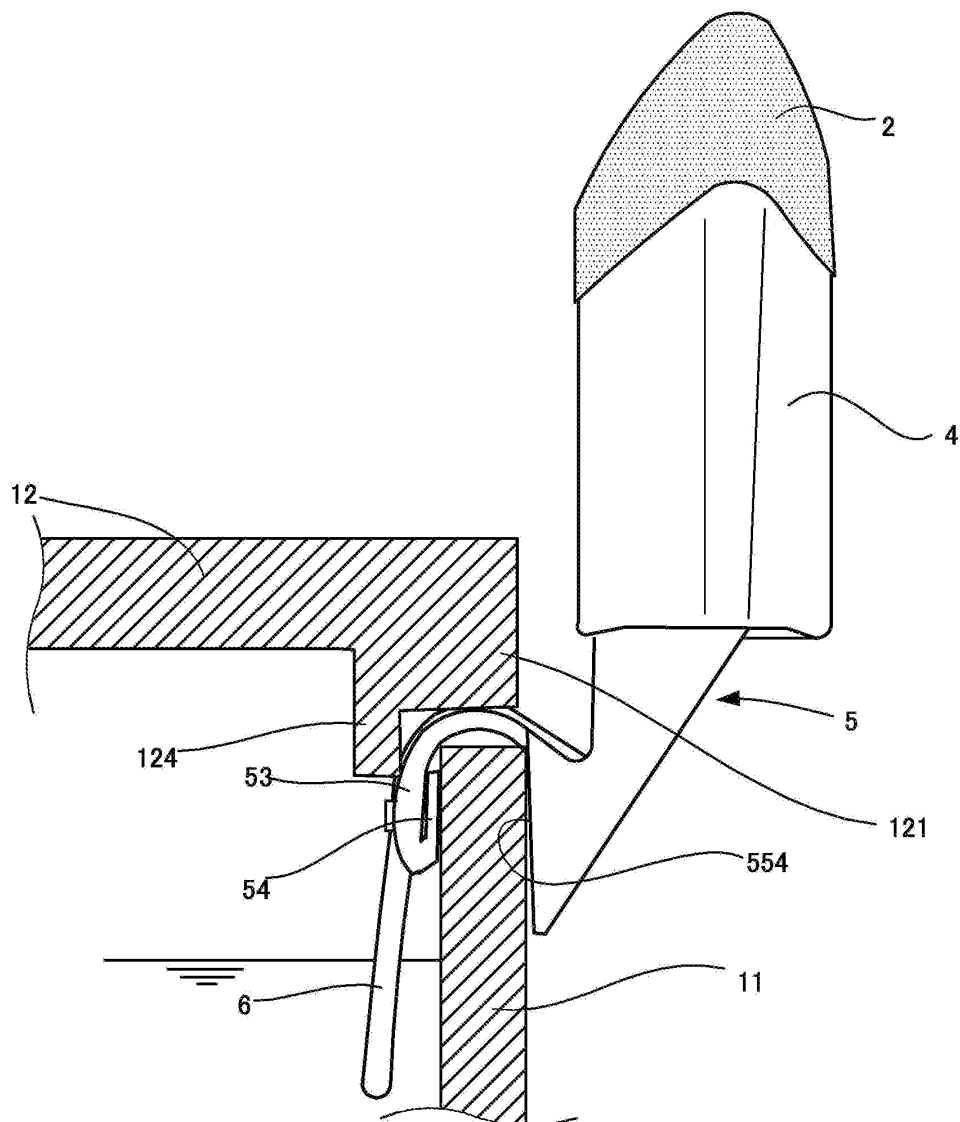
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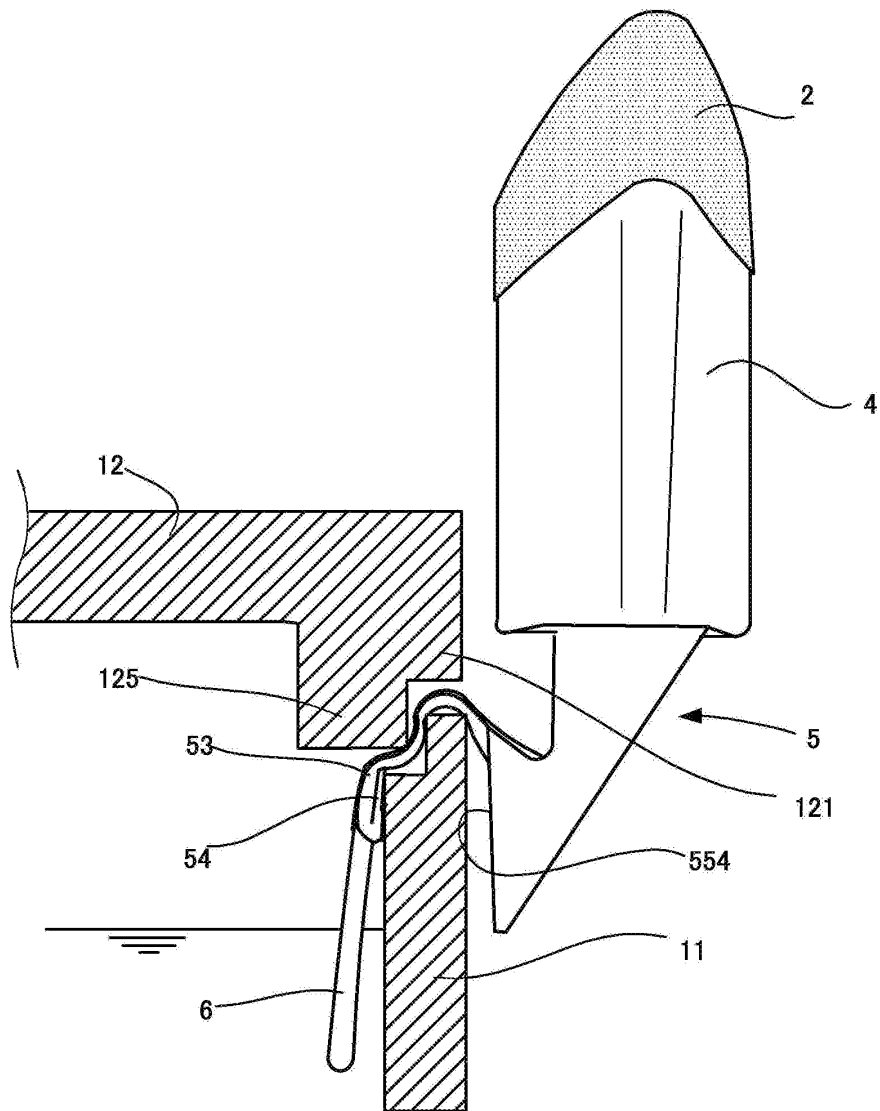
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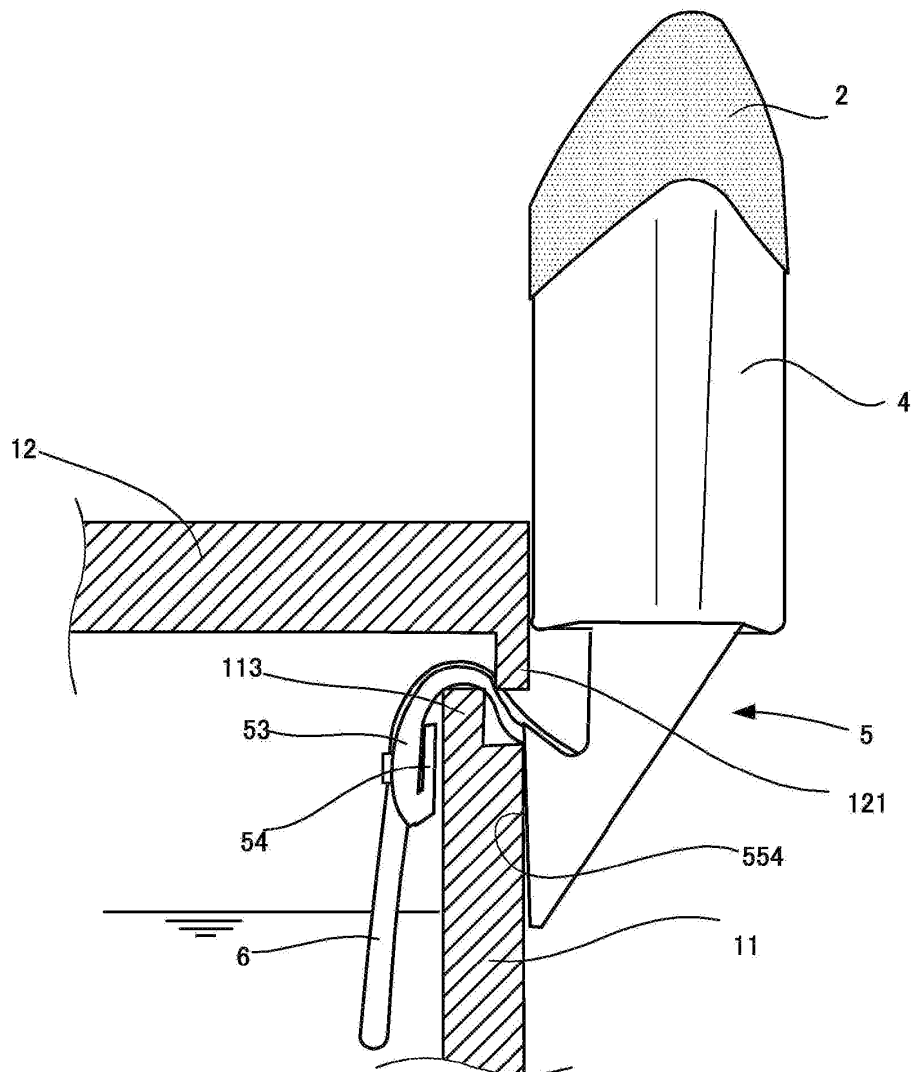
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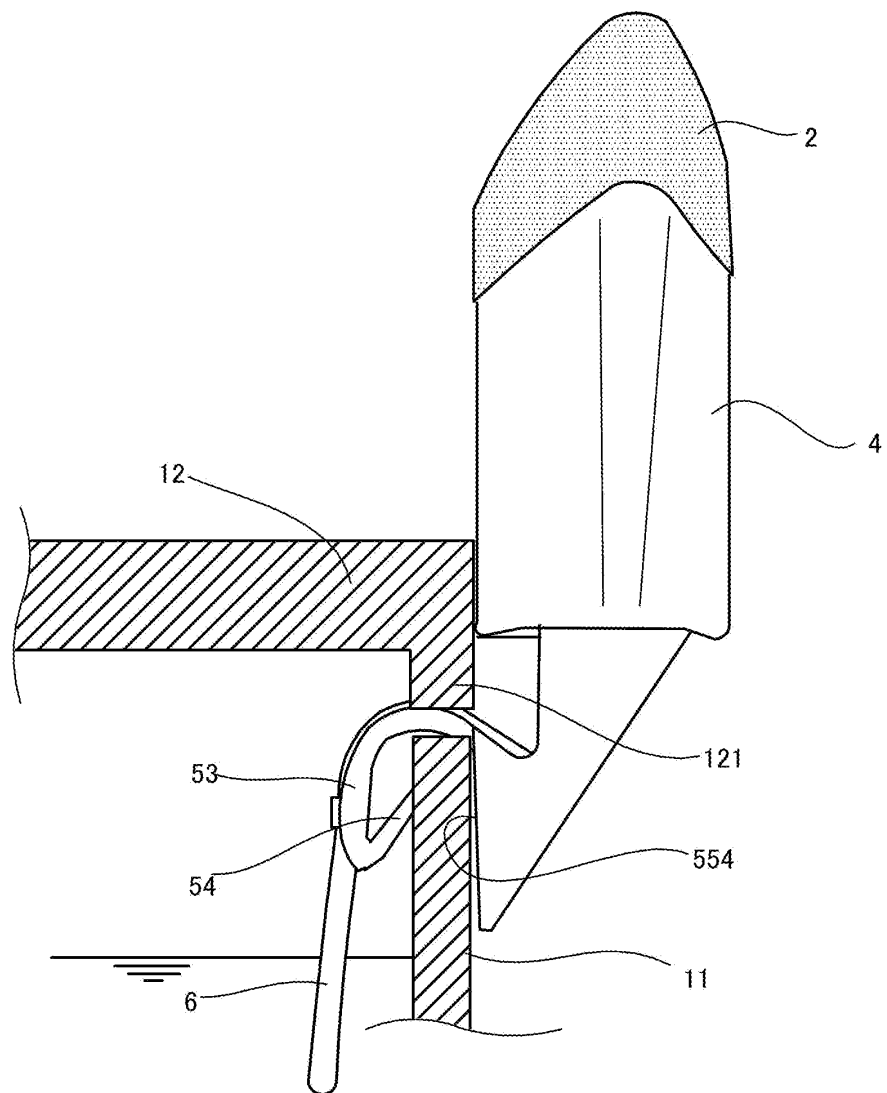
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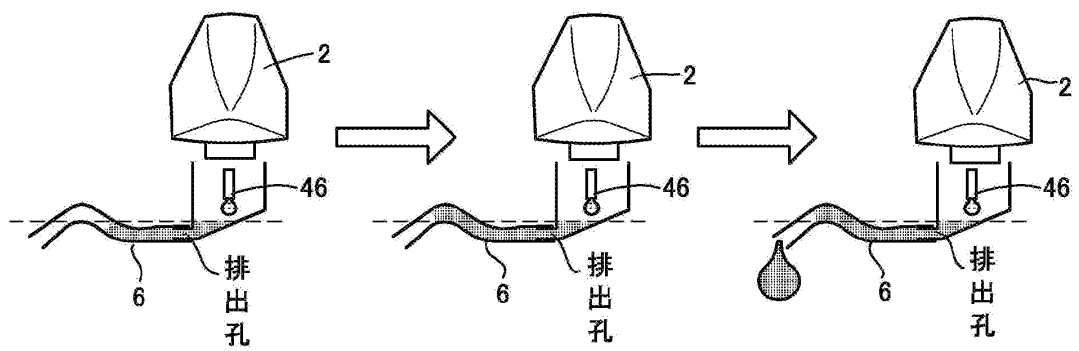
[図22]



[図23]



[図24]



[図25]

